Silicon PNP Power Transistors 2SA1265N

DESCRIPTION

- With TO-3P(I) package
- Complement to type 2SC3182
- 2SA1265 with short pin

APPLICATIONS

- Power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

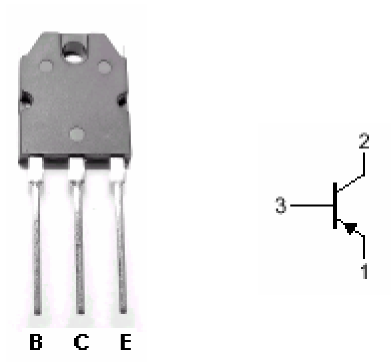

Fig.1 simplified outline (TO-3P(I)) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-140	V
V_{CEO}	Collector-emitter voltage	Open base	-140	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-10	A
I_B	Base current		-1	A
P_T	Total power dissipation	T_C=25□	100	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-50mA ,I_B=0	-140			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-7A; I_B=-0.7A		-0.8	-2.0	V
V_{BE}	Base-emitter voltage	I_C=-5A ; V_{CE}=-5V		-1.0	-1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=-140V; I_E=0			-5	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-5	μA
h_{FE-1}	DC current gain	I_C=-1A ; V_{CE}=-5V	55		160	
h_{FE-2}	DC current gain	I_C=-5A ; V_{CE}=5V	35			
f_T	Transition frequency	I_C=-1A ; V_{CE}=-5V		30		MHz
C_{ob}	Output capacitance	I_E=0 ; V_{CB}=10V ;f=1MHz		480		pF

◆ h_{FE-1} Classifications

R	O
55-110	80-160

PACKAGE OUTLINE

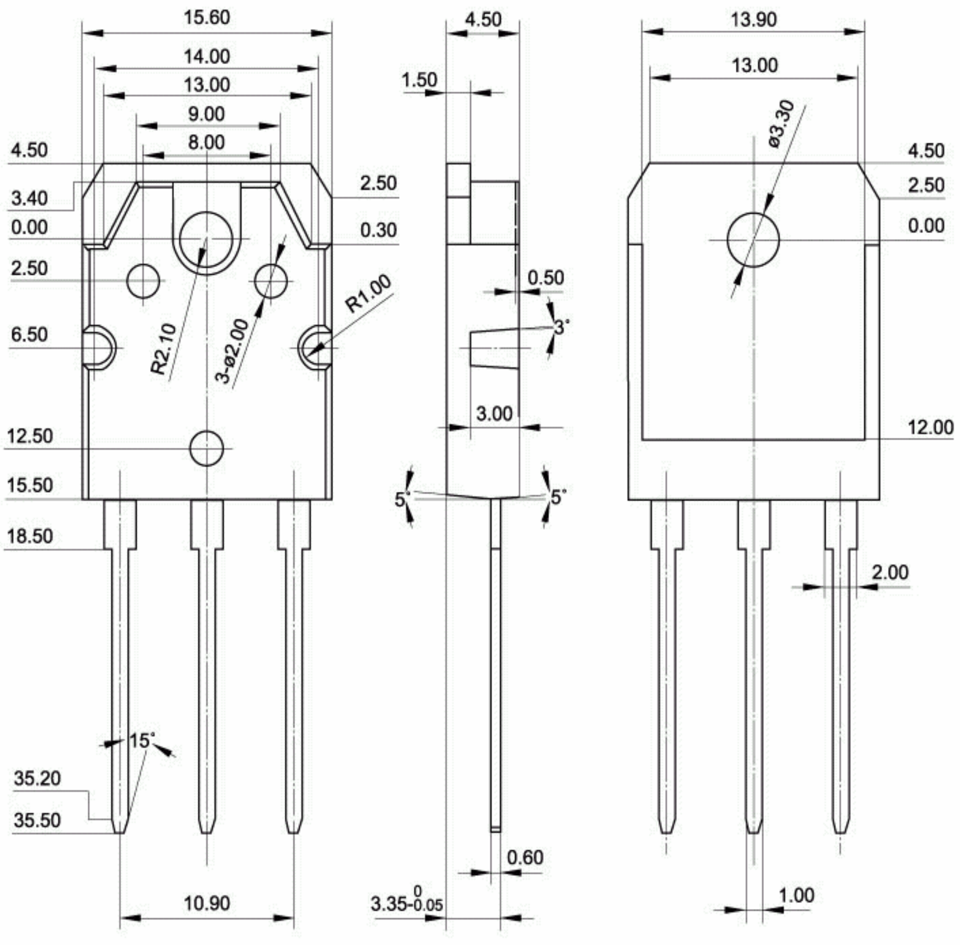

Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)

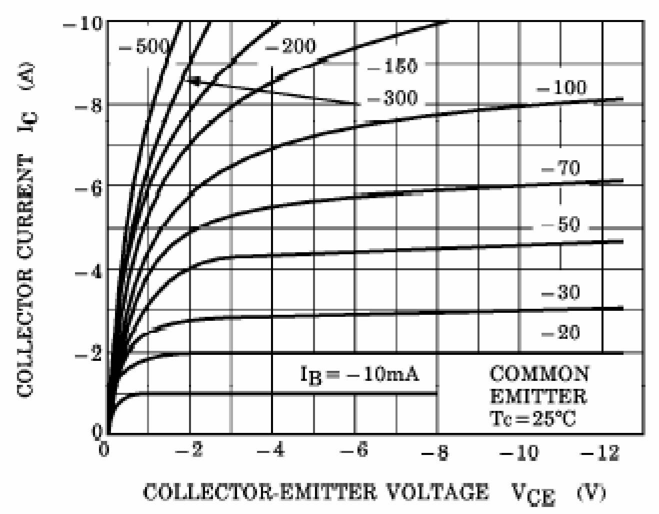

Fig.3 DC current Gain

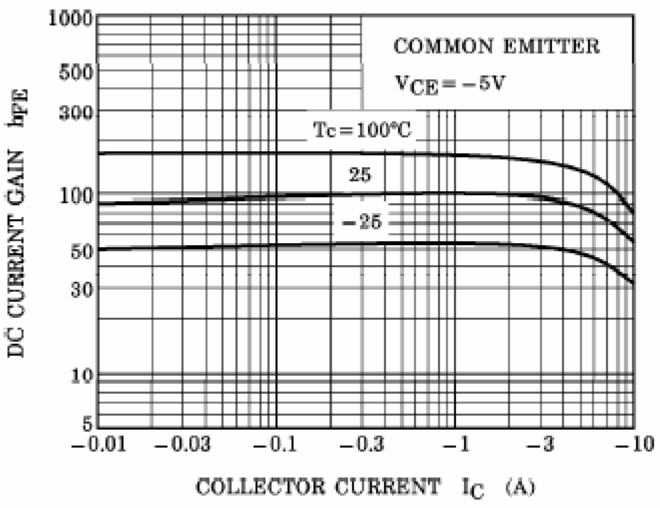

Fig.4 DC current Gain

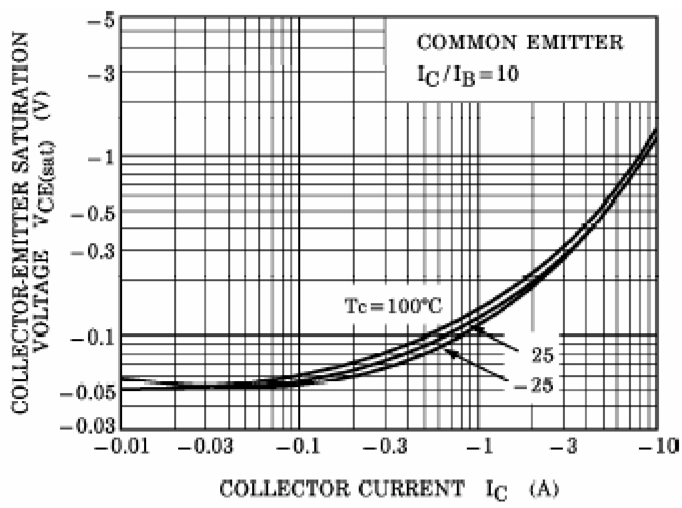

Fig.5 Collector-Emitter Saturation Voltage

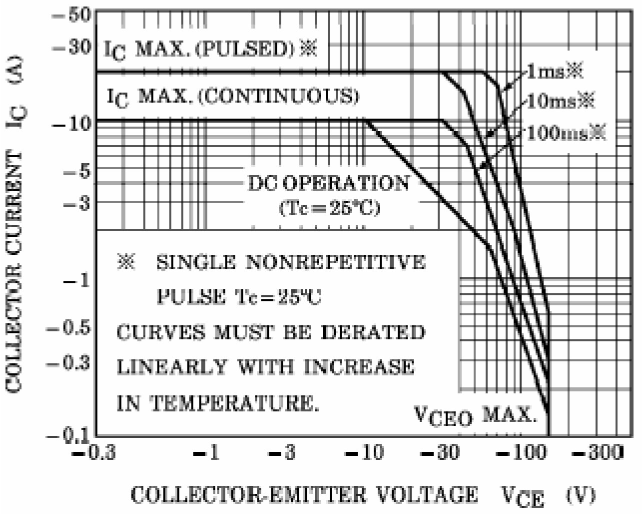

Fig.6 Safe Operating Area